



MEMC TO-01-2450 (3009)
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Falster et al
Serial No. 10/615,127
Filed July 24, 2003
Confirmation No. 8157

For PROCESS FOR PREPARING A STABILIZED IDEAL OXYGEN PRECIPITATING
SILICON WAFER

October 17, 2003

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INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. 1.97 and 1.98 and MPEP 609, and in compliance with the
duty of disclosure set forth in 37 C.F.R. 1.56, applicants submit copies of the references listed
* on the attached PTO/SB/08A for consideration by the Patent and Trademark Office in the above-
entitled application and to be made of record therein.

Respectfully submitted,

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PTO/SB/08A		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/615,127
		Filing Date	July 24, 2003
		Confirmation Number	8157
		First Named Inventor	Falster et al
		Group Art Unit	
		Examiner Name	
Sheet 1 of 4	Attorney Docket No.	MEMC TP-01-2450 (3009)	

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
	1	4,314,595		Yamamoto et al	02/09/1982
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	3	4,437,922		Bischoff et al	03/20/1984
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached..

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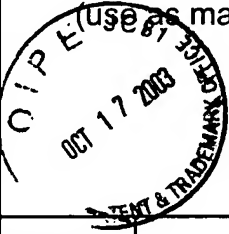
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ⁶
		Office	Number ⁴	Kind Code ² (if known)			
	25	DE	43 23 964	A1	Nadahara et al	01/20/1994	
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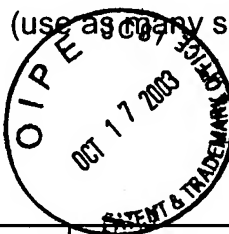
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
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